# DATA SHEET

# TDA8060TS
## Satellite ZERO-IF QPSK down-converter

Product specification
Supersedes data of 1998 May 29
File under Integrated Circuits, IC02

1999 Aug 30

Philips Semiconductors

# Satellite ZERO-IF QPSK down-converter TDA8060TS

## FEATURES

- Direct conversion QPSK demodulation (Zero IF)
- 920 to 2200 MHz range
- On-chip loop-controlled 0 or 90° phase shifter
- Variable gain on RF input
- 60 MHz, at –1 dB, bandwidth for baseband I and Q amplifiers
- Local oscillator output to PLL satellite or terrestrial
- 5 V supply voltage.

## APPLICATIONS

- Direct Broadcasting Satellite (DBS) QPSK demodulation
- Digital Video Broadcasting (DVB) QPSK deSupersedes data of 1998 May 29 modulation.

## GENERAL DESCRIPTION

The direct conversion QPSK demodulator is the front-end receiver dedicated to digital TV broadcasting, satisfying both DVB and DBS TV standards. The 920 to 2200 MHz wide range oscillator covers American, European and Asian satellite bands as well as the future SMA-TV US standard.

Accurate QPSK demodulation is ensured by the on-chip loop-controlled phase shifter. The Zero-IF concept discards traditional IF filtering and intermediate conversion techniques. It also simplifies the signal path.

The baseband I and Q signal bandwidth only depends, to a certain extent, on the external filter used in the application.

Optimum signal level is guaranteed by a gain-controlled amplifier at the RF input. The GAIN pin sets the gain for both I and Q channels, providing a 30 dB range.

The chip also offers a selectable internal LO prescaler (divide-by-2) and buffer that has been designed to be compatible with the input of a terrestrial or satellite frequency synthesizer.

## QUICK REFERENCE DATA

| SYMBOL | PARAMETER | MIN. | TYP. | MAX. | UNIT |
|---|---|---|---|---|---|
| $V_{CC}$ | supply voltage | 4.75 | 5.00 | 5.25 | V |
| $\Delta\Phi$ | quadrature error | – | – | 3 | deg |
| $f_{osc}$ | oscillator frequency | 920 | – | 2200 | MHz |
| $V_{o(p-p)}$ | output voltage (peak-to-peak value) | – | 0.75 | – | V |
| $T_{amb}$ | operating ambient temperature | –20 | – | +85 | °C |

## ORDERING INFORMATION

| TYPE NUMBER | PACKAGE | | |
|---|---|---|---|
| | NAME | DESCRIPTION | VERSION |
| TDA8060TS | SSOP24 | plastic shrink small outline package; 24 leads; body width 5.3 mm | SOT340-1 |

**BLOCK DIAGRAM**

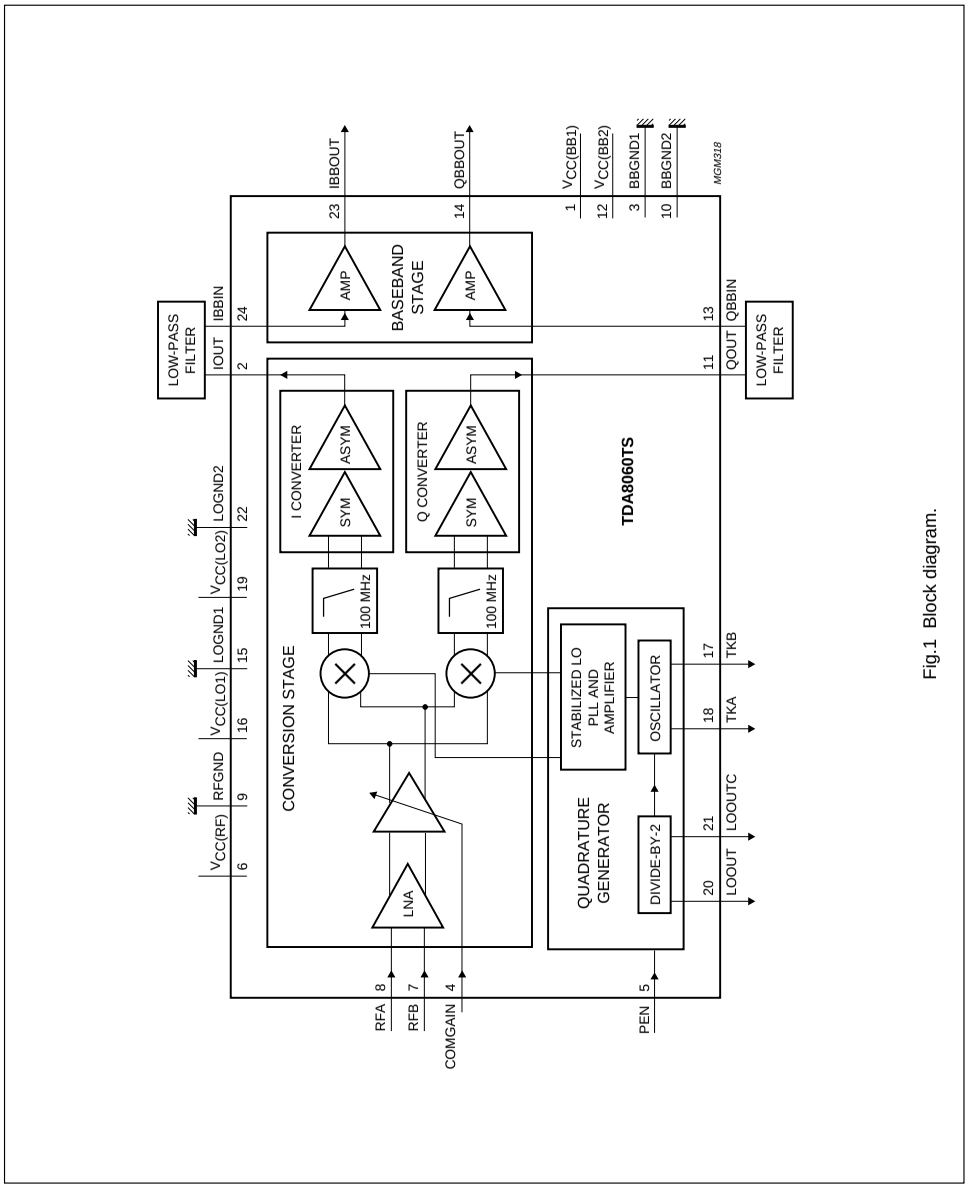



Fig.1 Block diagram.

## PINNING

| SYMBOL | PIN | DESCRIPTION |
|---|---|---|
| $V_{CC(BB1)}$ | 1 | supply voltage 1 for baseband circuit (+5 V) |
| IOUT | 2 | 'I' output from demodulator |
| BBGND1 | 3 | ground 1 for baseband circuit |
| COMGAIN | 4 | RF amplifier gain control input |
| PEN | 5 | prescaler enable |
| $V_{CC(RF)}$ | 6 | supply voltage for RF circuit (+5 V) |
| RFB | 7 | RF signal input B |
| RFA | 8 | RF signal input A |
| RFGND | 9 | ground for RF circuit |
| BBGND2 | 10 | ground 2 for baseband circuit |
| QOUT | 11 | 'Q' output from demodulator |
| $V_{CC(BB2)}$ | 12 | supply voltage 2 for baseband circuit (+5 V) |
| QBBIN | 13 | 'Q' baseband amplifier input |
| QBBOUT | 14 | 'Q' baseband amplifier output |
| LOGND1 | 15 | ground 1 for local oscillator circuit |
| $V_{CC(LO1)}$ | 16 | supply voltage 1 for local oscillator circuit (+5 V) |
| TKB | 17 | tank circuit input B |
| TKA | 18 | tank circuit input A |
| $V_{CC(LO2)}$ | 19 | supply voltage 2 for local oscillator circuit (+5 V) |
| LOOUT | 20 | local oscillator output to synthesizer divided or not according to PEN voltage |
| LOOUTC | 21 | |
| LOGND2 | 22 | ground 2 for local oscillator circuit |
| IBBOUT | 23 | 'I' baseband amplifier output |
| IBBIN | 24 | 'I' baseband amplifier input |

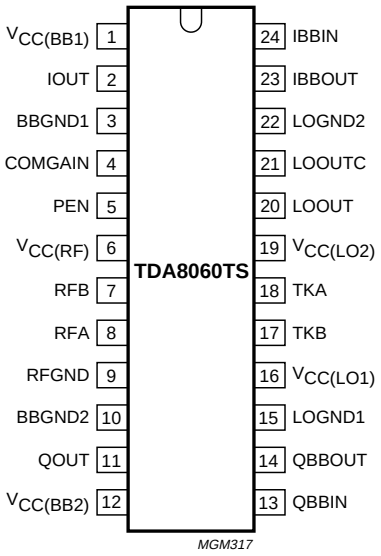



Fig.2 Pin configuration.

## LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL | PARAMETER | MIN. | MAX. | UNIT |
|---|---|---|---|---|
| $V_{CC}$ | supply voltage | –0.3 | +6.0 | V |
| $V_{i(max)}$ | maximum input voltage on all pins | –0.3 | $V_{CC}$ | V |
| $t_{sc(max)}$ | maximum short-circuit time | – | 10 | s |
| $T_{amb}$ | operating ambient temperature | –20 | +85 | °C |
| $T_{stg}$ | storage temperature | –55 | +150 | °C |
| $T_j$ | junction temperature | – | 150 | °C |

## HANDLING

Inputs and outputs are protected against electrostatic discharge in normal handling. However, to be totally safe, it is desirable to take normal precautions appropriate to handling MOS devices.

## THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|---|---|---|---|---|
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | in free air | 120 | K/W |

## DC CHARACTERISTICS

$T_{amb}$ = 25 °C; $V_{CC}$ = 5 V; unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|---|---|---|---|---|---|---|
| $V_{CC}$ | supply voltage | | 4.75 | 5.00 | 5.25 | V |
| $I_{CC}$ | supply current | PEN = 5 V | 63 | 73 | 83 | mA |
| | | PEN = 0 V | 60 | 70 | 80 | mA |
| **Conversion stage** | | | | | | |
| $V_{I(RFA)}$ | DC input voltage on pin RFA | | – | 0.9 | – | V |
| $V_{I(RFB)}$ | DC input voltage on pin RFB | | – | 0.9 | – | V |
| $V_{O(IOUT)}$ | DC output voltage on pin IOUT | | – | 2.0 | – | V |
| $V_{O(QOUT)}$ | DC output voltage on pin QOUT | | – | 2.0 | – | V |
| **Quadrature generator** | | | | | | |
| $V_{O(LOOUT)}$ | DC output voltage on pin LOOUT | | – | 4.7 | – | V |
| $V_{O(LOOUTC)}$ | DC output voltage on pin LOOUTC | | – | 4.7 | – | V |
| **Baseband stage** | | | | | | |
| $V_{I(IBBIN)}$ | DC input voltage on pin IBBIN | | – | 2.5 | – | V |
| $V_{I(QBBIN)}$ | DC input voltage on pin QBBIN | | – | 2.5 | – | V |
| $V_{O(IBBOUT)}$ | DC output voltage on pin IBBOUT | | – | 2.5 | – | V |
| $V_{O(QBBOUT)}$ | DC output voltage on pin QBBOUT | | – | 2.5 | – | V |

## AC CHARACTERISTICS

$T_{amb}$ = 25 °C; $V_{CC}$ = 5 V; unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|---|---|---|---|---|---|---|
| **Quadrature generator** | | | | | | |
| $f_{osc}$ | oscillator frequency range | | 920 | – | 2200 | MHz |
| $\Phi N_{osc}$ | oscillator phase noise | at 10 kHz offset; note 1 | – | –80 | –75 | dBc/Hz |
| $\lvert\Delta\Phi\rvert$ | absolute quadrature error | note 2 | – | 0 | 3 | deg |
| $f_{LOOUT}$ | output frequency | $V_{PEN}$ = 0 V | – | $f_{osc}$ | – | MHz |
| | | $V_{PEN} = V_{CC}$ | – | $\frac{1}{2}f_{osc}$ | – | MHz |
| $V_{o(diff)(LOOUT)}$ | differential output voltage at pin LOOUT | $R_L$ = 100 Ω differential | –30 | –22 | – | dBm |
| $\lvert Z_{o(diff)(LOOUT)}\rvert$ | differential output impedance at pin LOOUT | | – | 60 | – | Ω |
| **Conversion stage** | | | | | | |
| $R_{i(diff)}$ | series real part of differential input impedance at pins RFA and RFB | note 3 | – | 34 | – | Ω |
| $L_{i(diff)}$ | series inductance of differential input impedance at pins RFA and RFB | note 3 | – | 5 | – | nH |
| $P_{i(max)}$ | maximum input power per channel | | – | –22 | – | dBm |
| $P_{i(min)}$ | minimum input power per channel | | – | –52 | – | dBm |
| $\Delta G_v/\Delta V_{(slope)}$ | AGC slope | at $G_{v(RF\text{-}IOUT)(min)}$ | – | 30 | 40 | dB/V |
| $\Delta G_{v(I\text{-}Q)}$ | voltage gain mismatch between I and Q | | – | – | 1 | dB |
| $\Delta t_{d(g)(RF\text{-}IOUT)}$ | group delay variation per channel (40 MHz) from RF input to pin IOUT | | – | 0.5 | 2 | ns |
| $\Delta t_{d(g)(RF\text{-}QOUT)}$ | group delay variation per channel (40 MHz) from RF input to pin QOUT | | – | 0.5 | 2 | ns |
| $t_{d(g)(I\text{-}Q)(40)}$ | group delay mismatch per channel (40 MHz) between I and Q | | – | 0 | 0.5 | ns |
| $B_{(-1dB)(RF\text{-}IOUT)}$ | channel –1 dB bandwidth from RF input to pin IOUT | | 40 | 50 | – | MHz |
| $B_{(-1dB)(RF\text{-}QOUT)}$ | channel –1 dB bandwidth from RF input to pin QOUT | | 40 | 50 | – | MHz |
| $B_{(-3dB)(RF\text{-}IOUT)}$ | channel –3 dB bandwidth from RF input to pin IOUT | | 70 | 80 | – | MHz |
| $B_{(-3dB)(RF\text{-}QOUT)}$ | channel –3 dB bandwidth from RF input to pin QOUT | | 70 | 80 | – | MHz |
| $Z_{o(IOUT)}$ | output impedance at pin IOUT | | – | 65 | – | Ω |
| $Z_{o(QOUT)}$ | output impedance at pin QOUT | | – | 65 | – | Ω |
| $V_{o(IOUT)}$ | nominal output voltage level at pin IOUT | per channel | – | 25 | – | dBmV |
| $V_{o(QOUT)}$ | nominal output voltage level at pin QOUT | per channel | – | 25 | – | dBmV |
| $R_{oL(IOUT)}$ | resistive load at pin IOUT | | 400 | – | – | Ω |
| $R_{oL(QOUT)}$ | resistive load at pin QOUT | | 400 | – | – | Ω |

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|---|---|---|---|---|---|---|
| SYMMETRICAL RF INPUT (Fig.3) | | | | | | |
| $G_{v(RF-IOUT)(min)}$ | minimum voltage gain from RF input to pin IOUT | $V_{AGC}$ = 0.1 x $V_{CC}$; note 4 | – | – | –1 | dB |
| $G_{v(RF-IOUT)(max)}$ | maximum voltage gain from RF input to pin IOUT | $V_{AGC}$ = 0.9 x $V_{CC}$; note 4 | 28 | 29 | – | dB |
| $G_{v(RF-QOUT)(min)}$ | minimum voltage gain from RF input to pin QOUT | $V_{AGC}$ = 0.1 x $V_{CC}$; note 4 | – | – | –1 | dB |
| $G_{v(RF-QOUT)(max)}$ | maximum voltage gain from RF input to pin QOUT | $V_{AGC}$ = 0.9 x $V_{CC}$; note 4 | 28 | 29 | – | dB |
| $IP_{3i(I)}$ | I 3rd-order interception point at RF input | | 1 | 4 | – | dBm |
| $IP_{2i(I)}$ | I 2nd-order interception point at RF input | | 12 | 15 | – | dBm |
| $IP_{3i(Q)}$ | Q 3rd-order interception point at RF input | | 1 | 4 | – | dBm |
| $IP_{2i(Q)}$ | Q 2nd-order interception point at RF input | | 12 | 15 | – | dBm |
| $F_i$ | noise figure at maximum gain | $V_{AGC}$ = 0.9 x $V_{CC}$; $Z_{source}$ = 50 Ω | – | 12 | 15 | dB |
| ASYMMETRICAL RF INPUT (Fig.4) | | | | | | |
| $G_{v(RF-IOUT)(min)}$ | minimum voltage gain from RF input to pin IOUT | $V_{AGC}$ = 0.1 x $V_{CC}$; note 5 | – | – | –1 | dB |
| $G_{v(RF-IOUT)(max)}$ | maximum voltage gain from RF input to pin IOUT | $V_{AGC}$ = 0.9 x $V_{CC}$; note 5 | – | 29 | – | dB |
| $G_{v(RF-QOUT)(min)}$ | minimum voltage gain from RF input to pin QOUT | $V_{AGC}$ = 0.1 x $V_{CC}$; note 5 | – | – | –1 | dB |
| $G_{v(RF-QOUT)(max)}$ | maximum voltage gain from RF input to pin QOUT | $V_{AGC}$ = 0.9 x $V_{CC}$; note 5 | – | 29 | – | dB |
| $IP_{3i(I)}$ | I 3rd-order interception point at RF input | | – | 3 | – | dBm |
| $IP_{2i(I)}$ | I 2nd-order interception point at RF input | | – | 15 | – | dBm |
| $IP_{3i(Q)}$ | Q 3rd-order interception point at RF input | | – | 3 | – | dBm |
| $IP_{2i(Q)}$ | Q 2nd-order interception point at RF input | | – | 15 | – | dBm |
| $F_i$ | noise figure at maximum gain | $V_{AGC}$ = 0.9 x $V_{CC}$; $Z_{source}$ = 50 Ω | – | 13 | – | dB |
| **Baseband stages** | | | | | | |
| $Z_i$ | input impedance | | – | 10 | – | kΩ |
| $V_i$ | nominal input voltage level | per channel | – | 25 | – | dBmV |
| $NTX_i$ | number of channels at input | | – | 2 | – | – |
| $G_{v(IBBIN-IBBOUT)}$ | voltage gain from pin IBBIN to pin IBBOUT | | 19 | 20 | 22 | dB |
| $G_{v(QBBIN-QBBOUT)}$ | voltage gain from pin QBBIN to pin QBBOUT | | 19 | 20 | 22 | dB |
| $G_{v(I-Q)}$ | voltage gain mismatch between I and Q | | – | 0 | 1 | dB |
| $IP_{3i}$ | 3rd-order interception point at IQBBIN input | | 54 | 59 | – | dBmV |
| $IP_{2i}$ | 2nd-order interception point at IQBBIN input | | 72 | 79 | – | dBmV |
| $\Delta t_{d(g)(40)}$ | group delay variation in 40 MHz bandwidth | | – | 0.5 | 2 | ns |
| $t_{d(g)(I-Q)(40)}$ | group delay mismatch in 40 MHz band between I and Q | | – | 0.5 | 2 | ns |

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|---|---|---|---|---|---|---|
| $B_{(-1dB)}$ | channel –1 dB bandwidth | | 40 | 65 | – | MHz |
| $B_{(-3dB)}$ | channel –3 dB bandwidth | | 70 | 100 | – | MHz |
| $Z_o$ | output impedance | | – | 50 | – | Ω |
| $V_{o(p-p)}$ | nominal output voltage level | | – | 750 | – | mV |
| $R_{o(L)}$ | resistive load at output | | 400 | – | – | Ω |
| **Overall with a 100 nF capacitor instead of LP1 and LP2** | | | | | | |
| $t_{d(g)(I-Q)(40)}$ | group delay mismatch in 40 MHz band between I and Q | | – | 0.5 | 2 | ns |
| $t_{d(g)(I-Q)(R40)}$ | group delay ripple in 40 MHz band for I or Q | | – | 0.5 | 1 | ns |
| $G_{v(I-Q)(40)}$ | voltage gain mismatch in 40 MHz band between I and Q | | – | – | 1 | dB |
| $G_{R(I-Q)(40)}$ | voltage gain ripple in 40 MHz band for I or Q | | – | – | 1 | dB |
| SYMMETRICAL RF INPUT | | | | | | |
| $G_{v(RF-IBBOUT)(min)}$ | minimum voltage gain from RF input to pin IBBOUT | $V_{AGC} = 0.1 \times V_{CC}$; | – | – | 19 | dB |
| $G_{v(RF-IBBOUT)(max)}$ | maximum voltage gain from RF input to pin IBBOUT | $V_{AGC} = 0.9 \times V_{CC}$; | 48 | 49 | – | dB |
| $G_{v(RF-QBBOUT)(min)}$ | minimum voltage gain from RF input to pin QBBOUT | $V_{AGC} = 0.1 \times V_{CC}$; | – | – | 19 | dB |
| $G_{v(RF-QBBOUT)(max)}$ | maximum voltage gain from RF input to pin QBBOUT | $V_{AGC} = 0.9 \times V_{CC}$; | 48 | 49 | – | dB |
| $F_i$ | noise figure at maximum gain | $V_{AGC} = 0.9 \times V_{CC}$; $Z_{source} = 50\ \Omega$ | – | 13 | 16 | dB |
| ASYMMETRICAL RF INPUT | | | | | | |
| $G_{v(RF-IBBOUT)(min)}$ | minimum voltage gain from RF input to pin IBBOUT | $V_{AGC} = 0.1 \times V_{CC}$ | – | – | 19 | dB |
| $G_{v(RF-IBBOUT)(max)}$ | maximum voltage gain from RF input to pin IBBOUT | $V_{AGC} = 0.9 \times V_{CC}$ | – | 49 | – | dB |
| $G_{v(RF-QBBOUT)(min)}$ | minimum voltage gain from RF input to pin QBBOUT | $V_{AGC} = 0.1 \times V_{CC}$ | – | – | 19 | dB |
| $G_{v(RF-QBBOUT)(max)}$ | maximum voltage gain from RF input to pin QBBOUT | $V_{AGC} = 0.9 \times V_{CC}$ | – | 49 | – | dB |
| $F_i$ | noise figure at maximum gain | $V_{AGC} = 0.9 \times V_{CC}$; $Z_{source} = 50\ \Omega$ | – | 14 | – | dB |

**Notes**

1. Measured in baseband (at pin IOUT or pin QOUT) on a carrier at 2 MHz and 25 dBmV.
2. Quadrature error with respect to 90°.
3. The differential input impedance of the IC is 34 Ω in series with the IC pins which give an inductance of 5 nH. For optimum performance, this inductance should be cancelled by a matching network. Coupling capacitors of 1 pF give an acceptable result.
4. Gain = $V_{o(dB)} - V_{i(dB)}$ (see Fig.3). Gain for symmetrical RF input
5. Gain = $V_{o(dB)} - V_{i(dB)}$ (see Fig.3). Gain for asymmetrical RF input

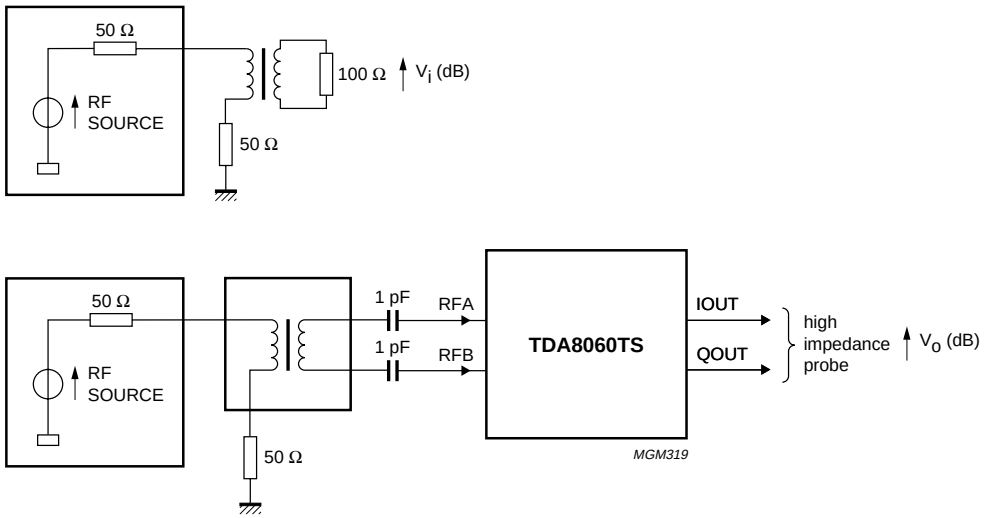



Fig.3 Gain control diagram for symmetrical RF input.

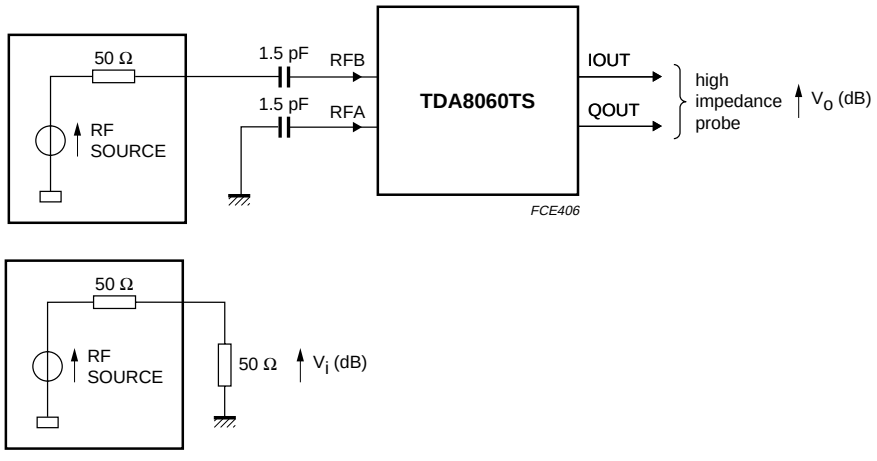



Fig.4 Gain control diagram for asymmetrical RF input

## APPLICATION INFORMATION

Close attention should be paid to the design of the external tank circuit of the VCO so that it covers the 920 to 2200 MHz frequency range. Both series 6 Ω resistors kill all parasitic oscillations that could alter this frequency range. The BB835 Siemens varicap diodes are mentioned because they provide the highest $C_{max}/C_{min}$ ratio as well as the least parasitic elements in our frequency range. The U-shaped inductance can be printed with a total length of approximately 20 mm.

Filters LP1 and LP2 are not detailed in this data sheet because their design only depends on the global system. As the TDA8060 has been designed to be compatible with DVB, DSS and Asian DVB, the cut-off frequencies and the tolerance in group delay, the orders of the filters cannot be globally established.

Nevertheless, TDA8060 internally filters the baseband at 100 MHz and the nominal levels at inputs and outputs mentioned in the specification table should be respected. The input impedance of LP1 and LP2 must exceed 400 Ω to avoid signal distortion.

The converter outputs (pin IOUT and pin QOUT) must be AC-coupled via the low-pass filter to the baseband amplifiers inputs (pin IBBIN and pin QBBIN). Because of the high impedance at pin IQBBIN, a 100 nF capacitor gives a high-pass frequency of 160 Hz.

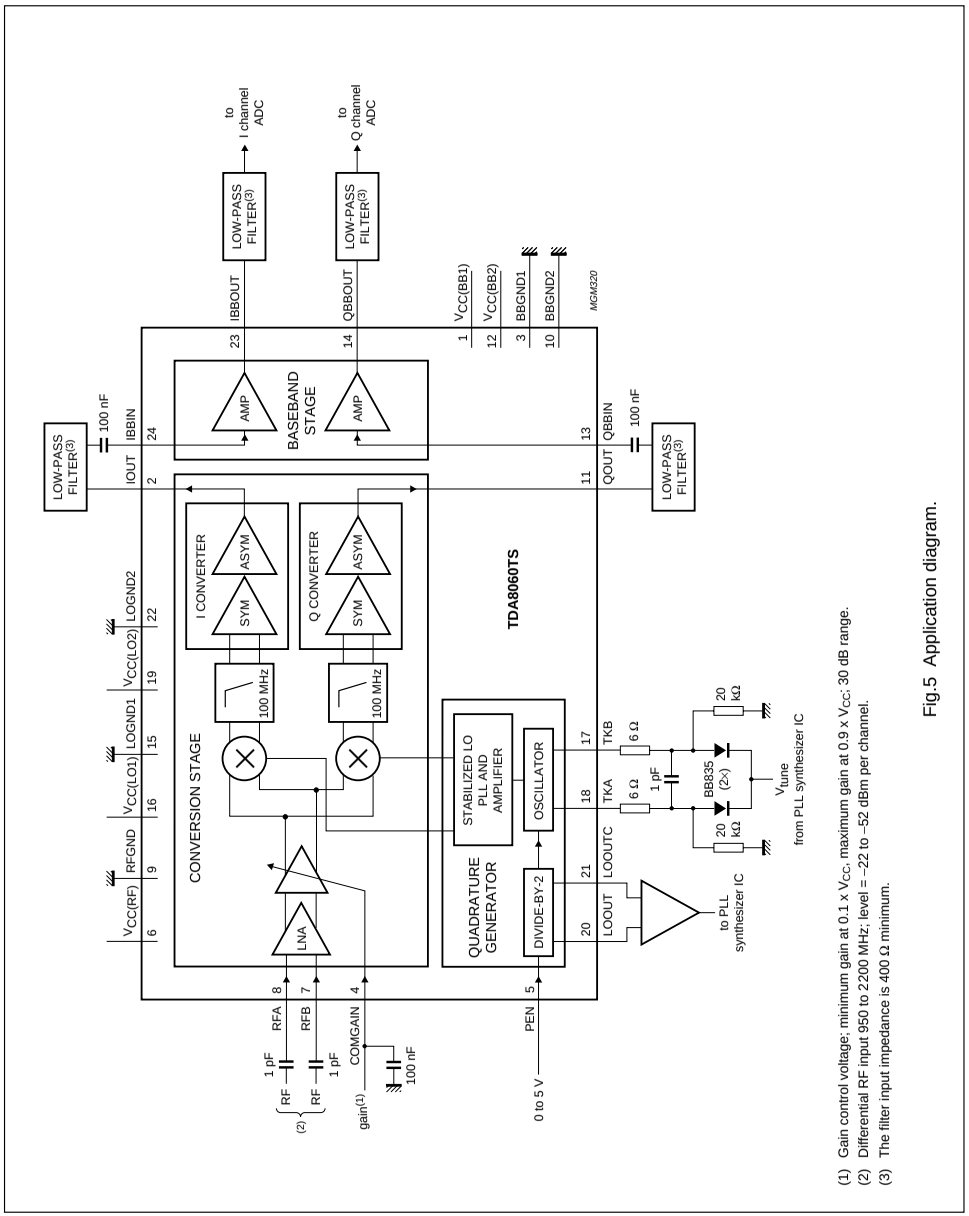
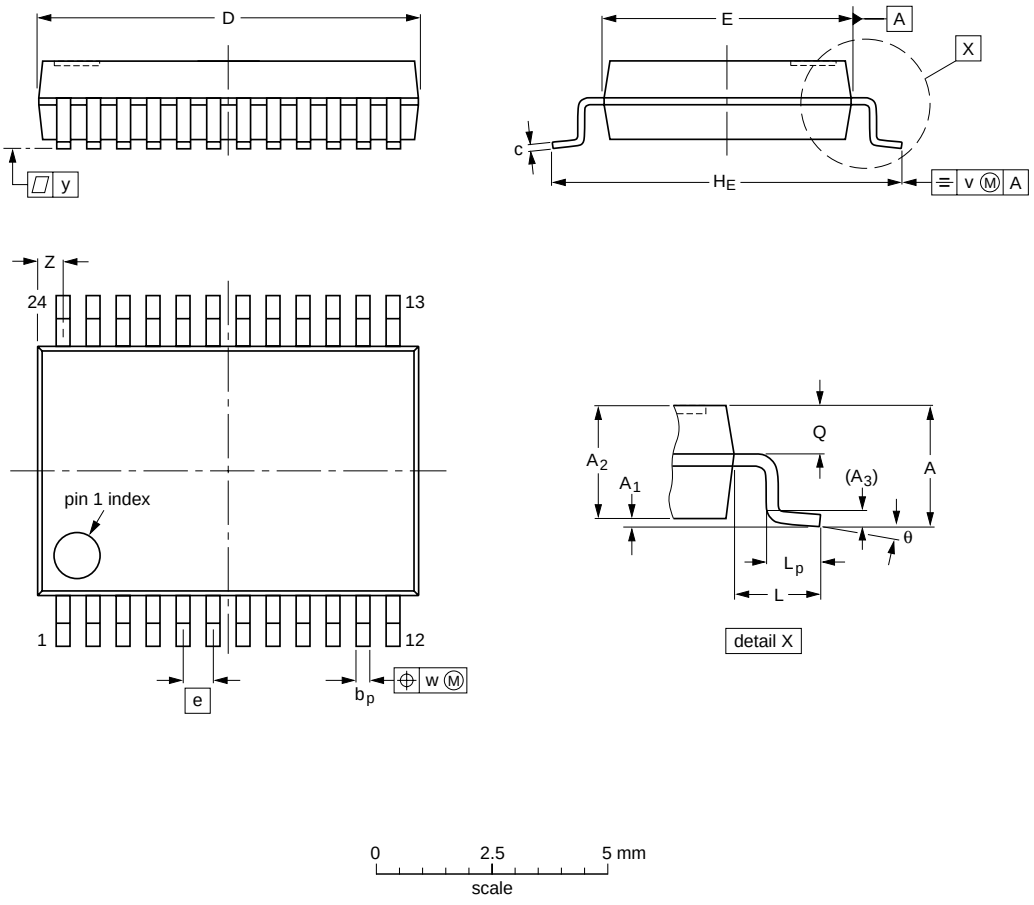



Fig.5 Application diagram.

(1) Gain control voltage; minimum gain at 0.1 x $V_{CC}$, maximum gain at 0.9 x $V_{CC}$; 30 dB range.
(2) Differential RF input 950 to 2200 MHz; level = −22 to −52 dBm per channel.
(3) The filter input impedance is 400 Ω minimum.

## PACKAGE OUTLINE

**SSOP24: plastic shrink small outline package; 24 leads; body width 5.3 mm** **SOT340-1**




**DIMENSIONS (mm are the original dimensions)**

| UNIT | A max. | $A_1$ | $A_2$ | $A_3$ | $b_p$ | c | $D^{(1)}$ | $E^{(1)}$ | e | $H_E$ | L | $L_p$ | Q | v | w | y | $Z^{(1)}$ | θ |
|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|---|
| mm | 2.0 | 0.21<br>0.05 | 1.80<br>1.65 | 0.25 | 0.38<br>0.25 | 0.20<br>0.09 | 8.4<br>8.0 | 5.4<br>5.2 | 0.65 | 7.9<br>7.6 | 1.25 | 1.03<br>0.63 | 0.9<br>0.7 | 0.2 | 0.13 | 0.1 | 0.8<br>0.4 | $8^o$<br>$0^o$ |

**Note**

1. Plastic or metal protrusions of 0.20 mm maximum per side are not included.

| OUTLINE VERSION | REFERENCES | | | | EUROPEAN PROJECTION | ISSUE DATE |
|---|---|---|---|---|---|---|
| | IEC | JEDEC | EIAJ | | | |
| SOT340-1 | | MO-150AG | | | | ~~93-09-08~~<br>95-02-04 |

## SOLDERING

### Introduction to soldering surface mount packages

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *"Data Handbook IC26; Integrated Circuit Packages"* (document order number 9398 652 90011).

There is no soldering method that is ideal for all surface mount IC packages. Wave soldering is not always suitable for surface mount ICs, or for printed-circuit boards with high population densities. In these situations reflow soldering is often used.

### Reflow soldering

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several methods exist for reflowing; for example, infrared/convection heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 and 200 seconds depending on heating method.

Typical reflow peak temperatures range from 215 to 250 °C. The top-surface temperature of the packages should preferable be kept below 230 °C.

### Wave soldering

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

To overcome these problems the double-wave soldering method was specifically developed.

If wave soldering is used the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.
- For packages with leads on two sides and a pitch (e):
  - larger than or equal to 1.27 mm, the footprint longitudinal axis is **preferred** to be parallel to the transport direction of the printed-circuit board;
  - smaller than 1.27 mm, the footprint longitudinal axis **must** be parallel to the transport direction of the printed-circuit board.

  The footprint must incorporate solder thieves at the downstream end.
- For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time is 4 seconds at 250 °C.
A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

### Manual soldering

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C.

When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 °C.

**Suitability of surface mount IC packages for wave and reflow soldering methods**

| PACKAGE | SOLDERING METHOD | |
|---|---|---|
| | WAVE | REFLOW(1) |
| BGA, SQFP | not suitable | suitable |
| HLQFP, HSQFP, HSOP, HTSSOP, SMS | not suitable(2) | suitable |
| PLCC(3), SO, SOJ | suitable | suitable |
| LQFP, QFP, TQFP | not recommended(3)(4) | suitable |
| SSOP, TSSOP, VSO | not recommended(5) | suitable |

**Notes**

1. All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect). For details, refer to the Drypack information in the *"Data Handbook IC26; Integrated Circuit Packages; Section: Packing Methods"*.
2. These packages are not suitable for wave soldering as a solder joint between the printed-circuit board and heatsink (at bottom version) can not be achieved, and as solder may stick to the heatsink (on top version).
3. If wave soldering is considered, then the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.
4. Wave soldering is only suitable for LQFP, TQFP and QFP packages with a pitch (e) equal to or larger than 0.8 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.65 mm.
5. Wave soldering is only suitable for SSOP and TSSOP packages with a pitch (e) equal to or larger than 0.65 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.5 mm.

**DEFINITIONS**

| **Data sheet status** | |
|---|---|
| Objective specification | This data sheet contains target or goal specifications for product development. |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification | This data sheet contains final product specifications. |
| **Limiting values** | |
| Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability. | |
| **Application information** | |
| Where application information is given, it is advisory and does not form part of the specification. | |

**LIFE SUPPORT APPLICATIONS**

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

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